

P-Channel Enhancement Mode MOSFET

Feature

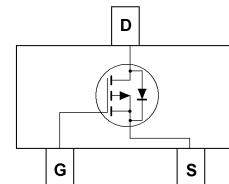
-20V/-2.5A RDS(ON) = 120mΩ(MAX) @VGS = -4.5V.

RDS(ON) = 150mΩ(MAX) @VGS = -2.5V.

Super High dense cell design for extremely low RDS(ON)

Reliable and Rugged

SC-59 for Surface Mount Package



SC-59

Applications

Power Management

Portable Equipment and Battery Powered Systems.

Absolute Maximum Ratings

TA=25°C Unless Otherwise noted

Parameter	Symbol	Limit	Units
Drain-Source Voltage	V _{DS}	-20	V
Gate-Source Voltage	V _{GS}	±10	V
Drain Current-Continuous	I _D	-2.5	A

Electrical Characteristics

TA=25°C Unless Otherwise noted

Parameter	Symbol	Test Conditions	Min	Typ.	Max	Units
Off Characteristics						
Drain to Source Breakdown Voltage	BVDSS	VGS=0V, ID=-250μA	-20	-	-	V
Zero-Gate Voltage Drain Current	IDSS	VDS=-20V, VGS=0V	-	-	-1	μA
Gate Body Leakage Current, Forward	IGSSF	VGS=10V, VDS=0V	-	-	100	nA
Gate Body Leakage Current, Reverse	IGSSR	VGS=-10V, VDS=0V	-	-	-100	nA
On Characteristics						
Gate Threshold Voltage	VGS(th)	VGS= VDS, ID=-250μA	-0.4	-	-1.0	V
Static Drain-source	RDS(ON)	VGS =-4.5V, ID =-2.5A	-	--	120	mΩ
On-Resistance		VGS =-2.5V, ID =-2.0A	-	--	150	mΩ
Drain-Source Diode Characteristics and Maximum Ratings						
Drain-Source Diode Forward Voltage	VSD	VGS =0V, IS=-1.25A			-1.2	V

Typical Characteristics

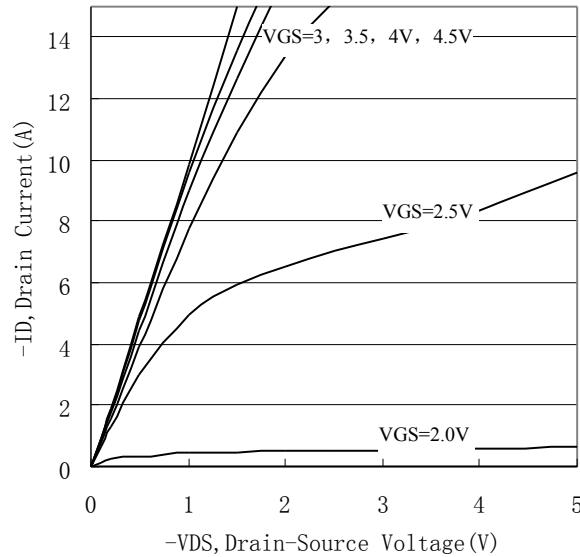


Figure 1. Output Characteristics

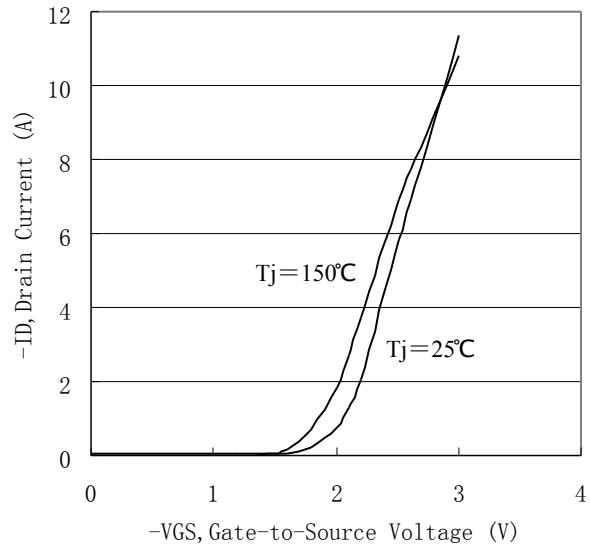


Figure 2. Transfer Characteristics

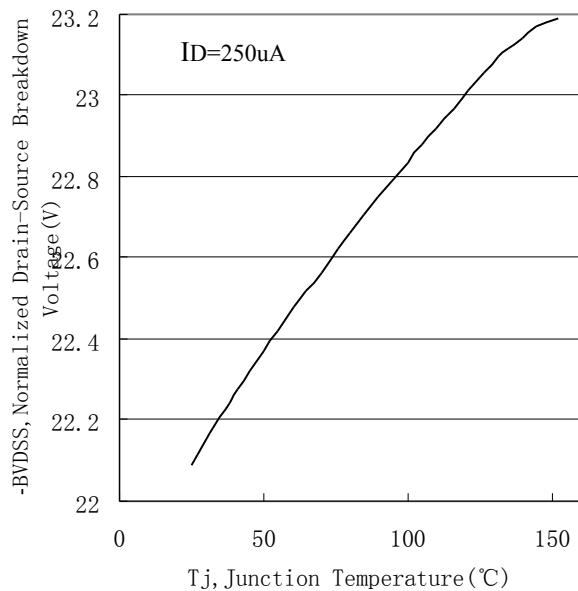


Figure 3. Breakdown Voltage Variation with Temperature

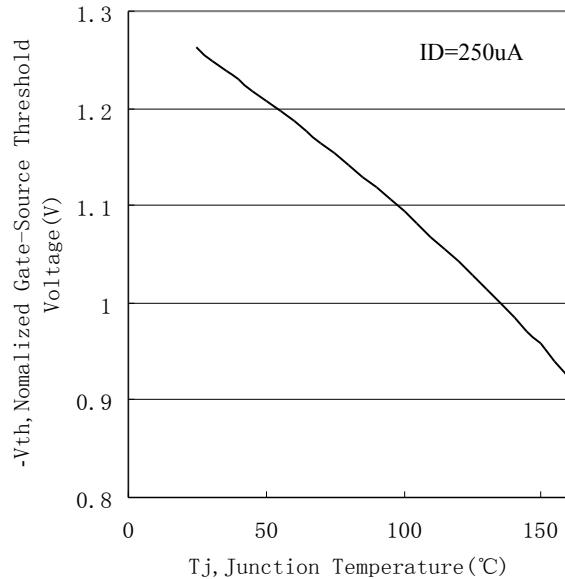
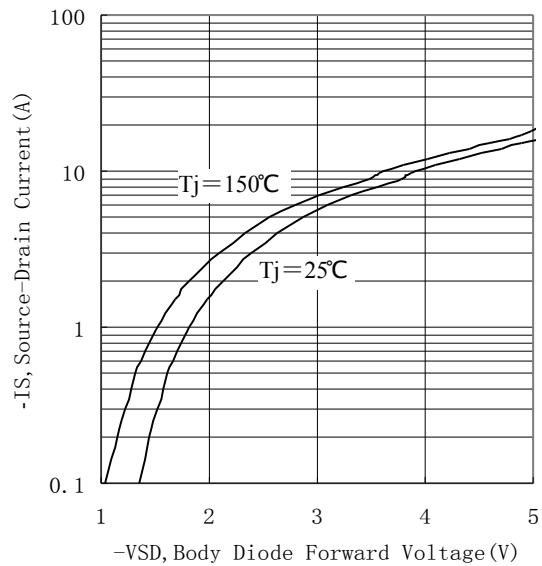
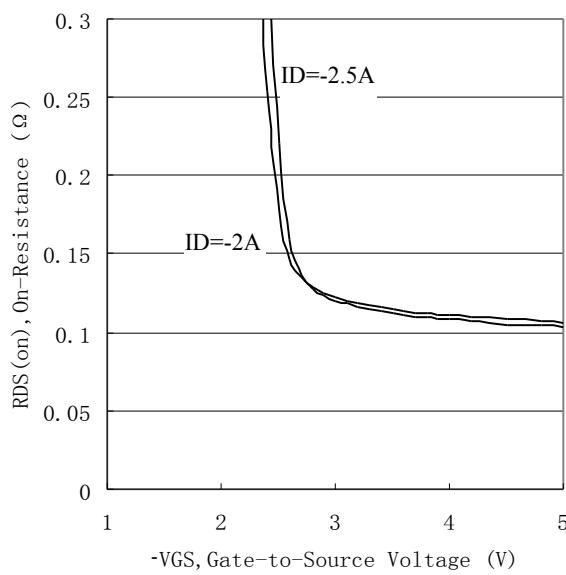
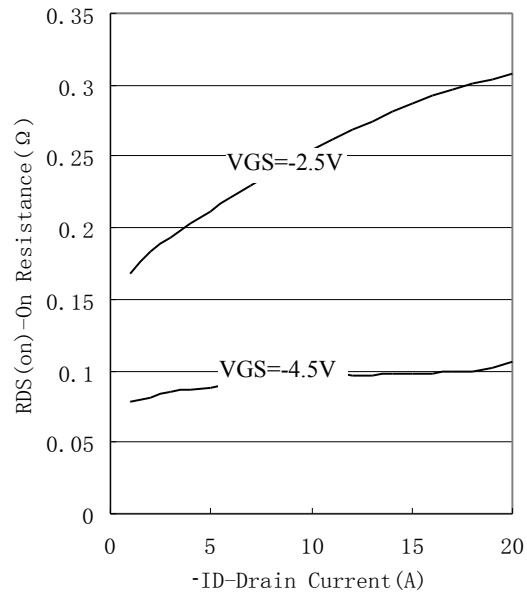
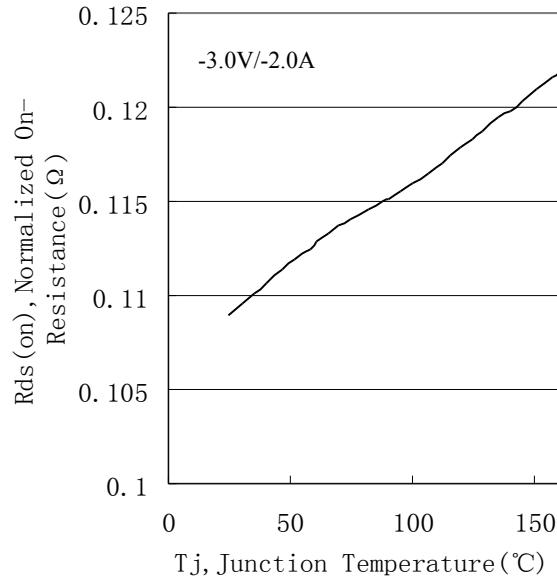


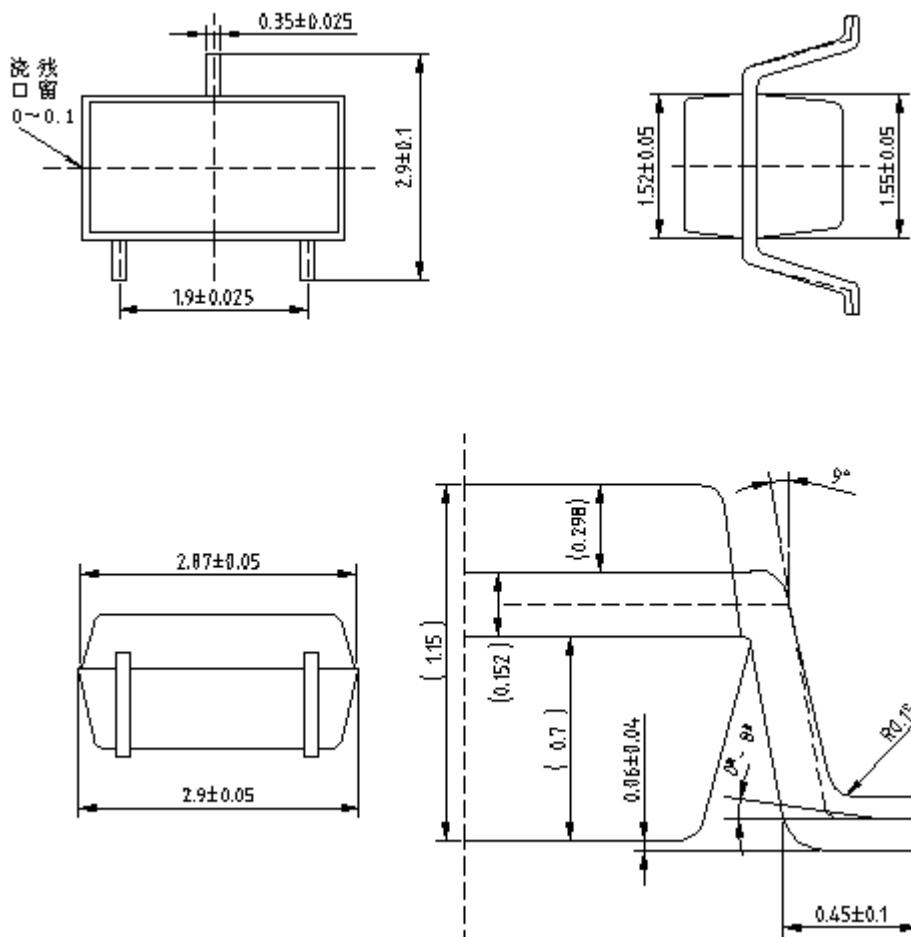
Figure 4. Gate Threshold Variation with Temperature

Typical Characteristics



Package Outline Dimensions (UNIT: mm)

SC-59



SC-59 Carrier Tape

